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May 2014

FDMC15N06

N-Channel UltraFET Power MOSFET

55 V, 15 A, 90 mΩ

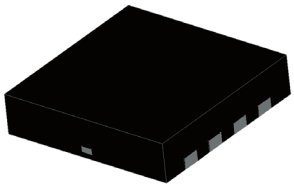
Features

- $R_{DS(on)}$ = 75 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 15 A
- 100% Avalanche Tested
- RoHS compliant

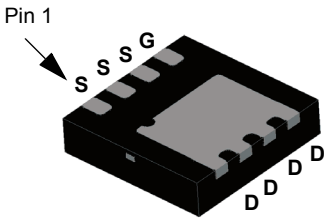
Description

These N-Channel power MOSFETs are manufactured using the innovative UltraFET process. This advanced process technology achieves the lowest possible on-resistance per silicon area, resulting in outstanding performance.This device is capable of withstanding high energy in the avalanche mode and the diode exhibits very low reverse recovery time and stored charge. It was designed for use in applications where power efficiency is important, such as switching regulators, switching converters, motor drivers, relay drivers, lowvoltage bus switches, and power management in portable and battery-operated products.

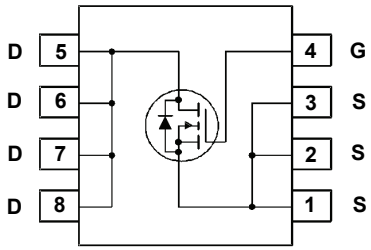
Top



Bottom



MLP 3.3x3.3



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			FDMC15N06	Unit
V_{DSS}	Drain to Source Voltage			55	V
V_{GSS}	Gate to Source Voltage			±20	V
I_D	Drain Current	- Continuous (T_C = 25°C)		15	A
		- Continuous (T_C = 100°C)		9	
		- Continuous (T_A = 25°C)	(Note 1a)	2.4	A
I_{DM}	Drain Current	- Pulsed	(Note 2)	60	A
E_{AS}	Single Pulsed Avalanche Energy		(Note 3)	36	mJ
I_{AR}	Avalanche Current			15	A
E_{AR}	Repetitive Avalanche Energy			3.5	mJ
P_D	Power Dissipation	(T_C = 25°C)		35	W
		(T_A = 25°C)		2.3	W
T_J, T_{STG}	Operating and Storage Temperature Range			-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8” from Case for 5 Seconds			300	°C

Thermal Characteristics

Symbol	Parameter		FDMC15N06	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.		3.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	(Note 1a)	53	

Package Marking and Ordering Information

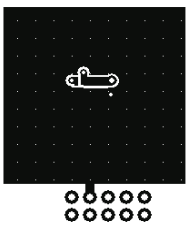
Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDMC15N06	15N06	Power 33	Tape and Reel	330 mm	12 mm	3000 units

Electrical Characteristics $T_C = 25^oC$ unless otherwise noted.

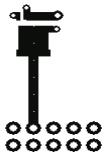
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V, T_C = 25°C	55	-	-	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	70	-	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 50 V, V_{GS} = 0 V	-	-	1	μA
		V_{DS} = 45 V, T_C = 150°C	-	-	250	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 15 A	-	0.075	0.090	Ω
g_{FS}	Forward Transconductance	V_{DS} = 20 V, I_D = 15 A	-	5	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz	-	265	350	pF
C_{oss}	Output Capacitance		-	97	130	pF
C_{rss}	Reverse Transfer Capacitance		-	28	42	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DS} = 30 V, I_D = 15 A, V_{GS} = 10 V (Note 4)	-	8.8	11.5	nC
Q_{gs}	Gate to Source Gate Charge		-	1.7	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	3.6	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 30 V, I_D = 15 A, V_{GS} = 10 V, R_G = 25 Ω (Note 4)	-	9.5	29	ns
t_r	Turn-On Rise Time		-	36.5	83	ns
$t_{d(off)}$	Turn-Off Delay Time		-	22.5	55	ns
t_f	Turn-Off Fall Time		-	22	54	ns
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	15	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	60	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 15 A	-	-	1.25	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_{SD} = 15 A, dI_F/dt = 100 A/μs (Note 5)	-	30	-	ns
Q_{rr}	Reverse Recovery Charge		-	35	-	nC

Notes:

1: $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 53 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b.125 °C/W when mounted on a minimum pad of 2 oz copper

2: Repetitive rating: pulse-width limited by maximum junction temperature.

3: L = 1 mH, I_{AS} = 8.5 A, R_G = 25 Ω, starting T_J = 25°C.

4: Essentially independent of operating temperature typical characteristics.

5: I_{SD} ≤ 15 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 40 V, starting T_J = 25°C.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

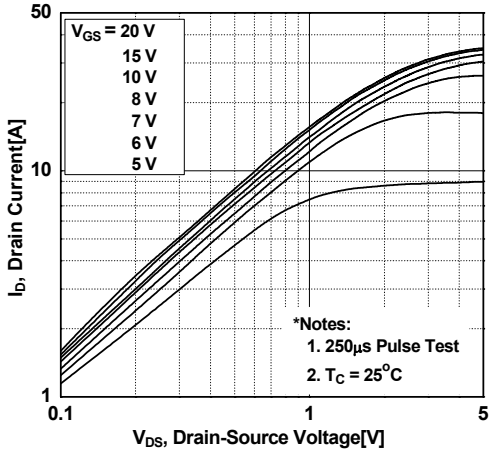


Figure 2. Transfer Characteristics

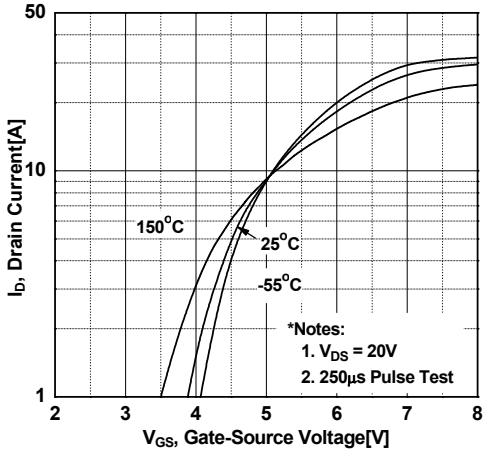


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

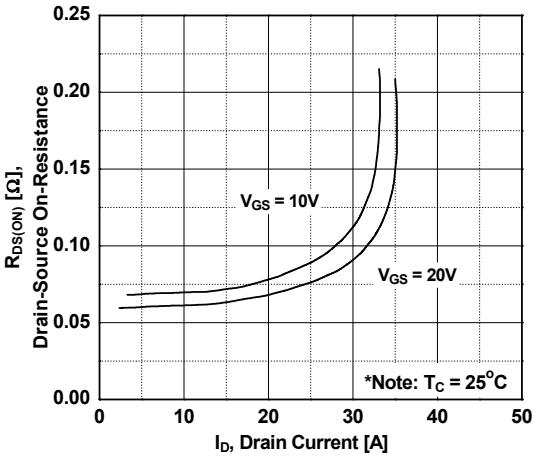


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

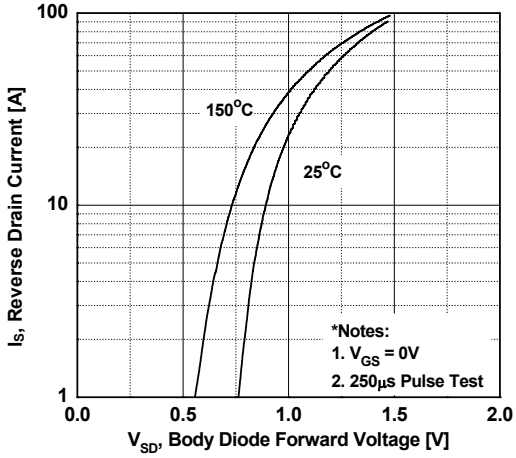


Figure 5. Capacitance Characteristics

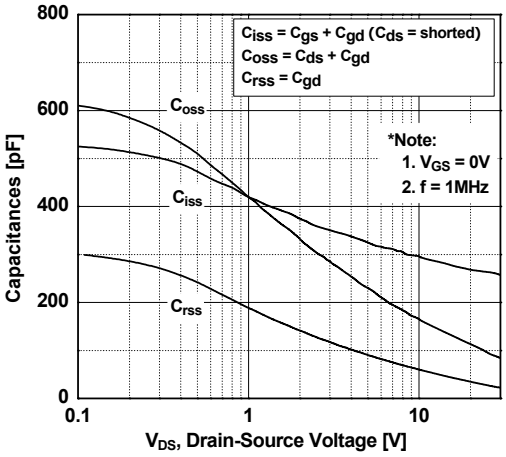
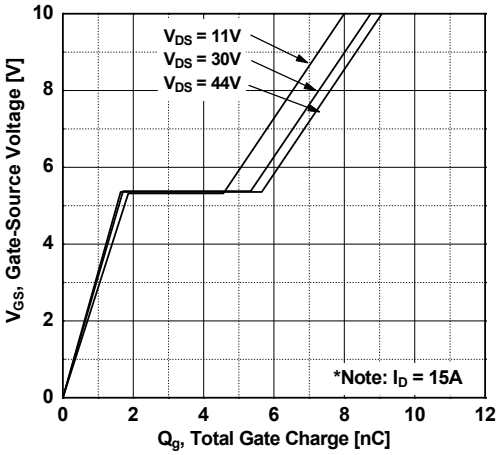


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

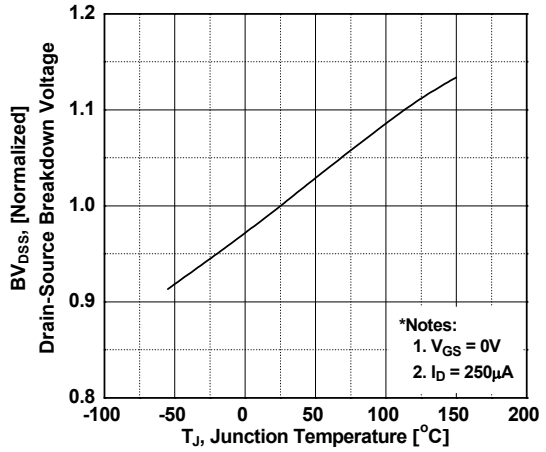


Figure 8. On-Resistance Variation vs. Temperature

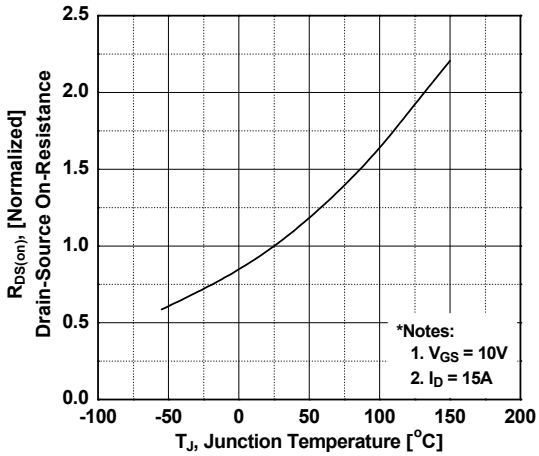


Figure 9. Maximum Safe Operating Area

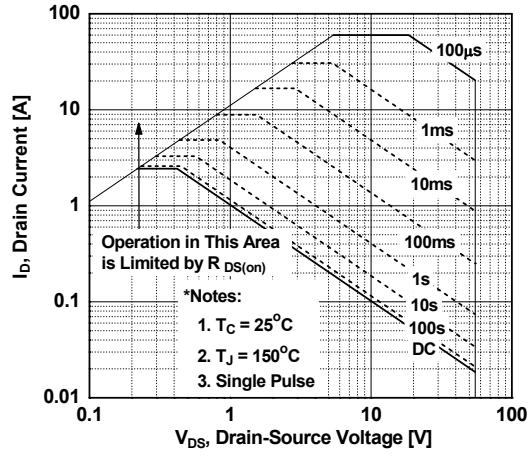


Figure 10. Maximum Drain Current vs. Case Temperature

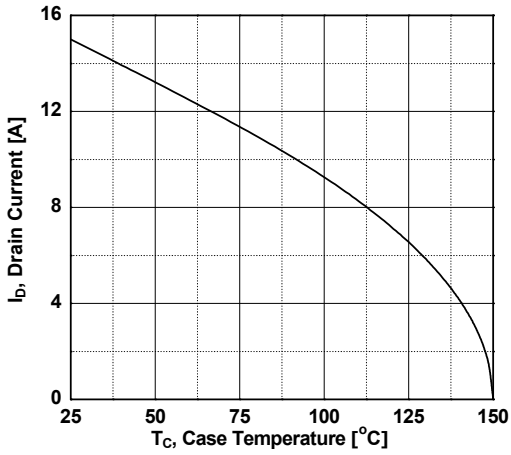
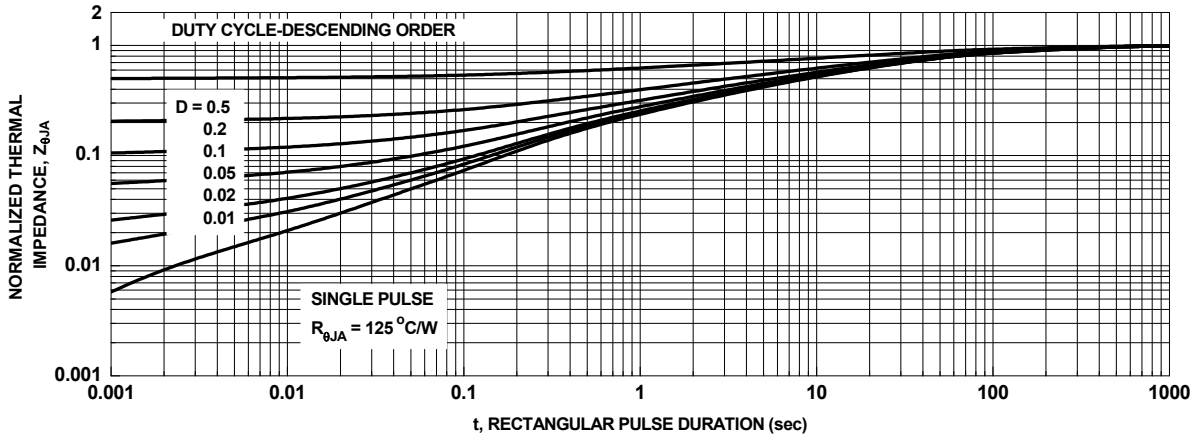


Figure 11. Transient Thermal Response Curve



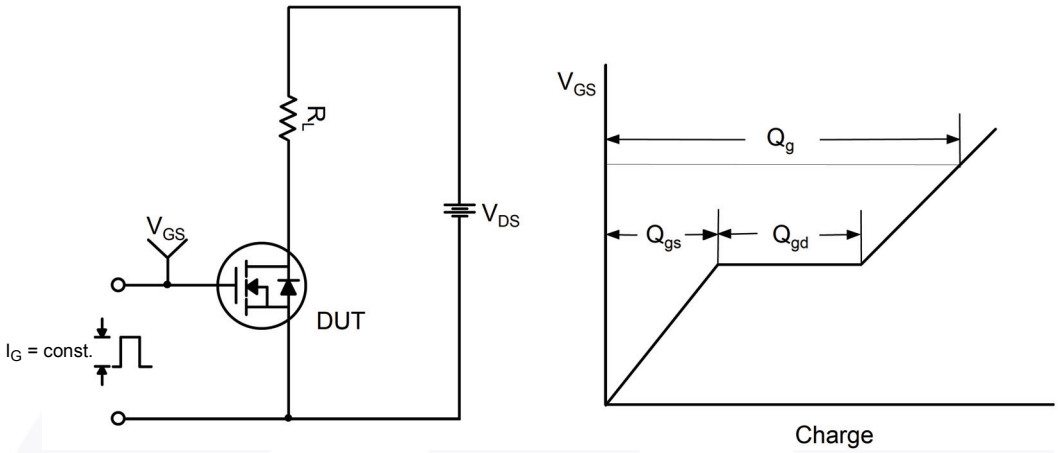


Figure 12. Gate Charge Test Circuit & Waveform

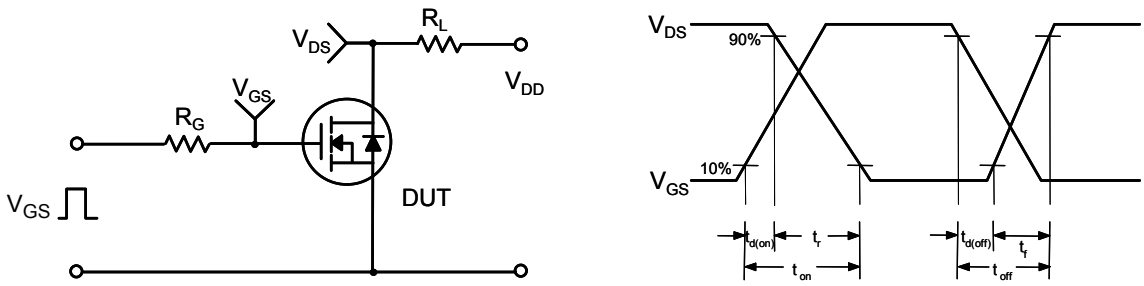


Figure 13. Resistive Switching Test Circuit & Waveforms

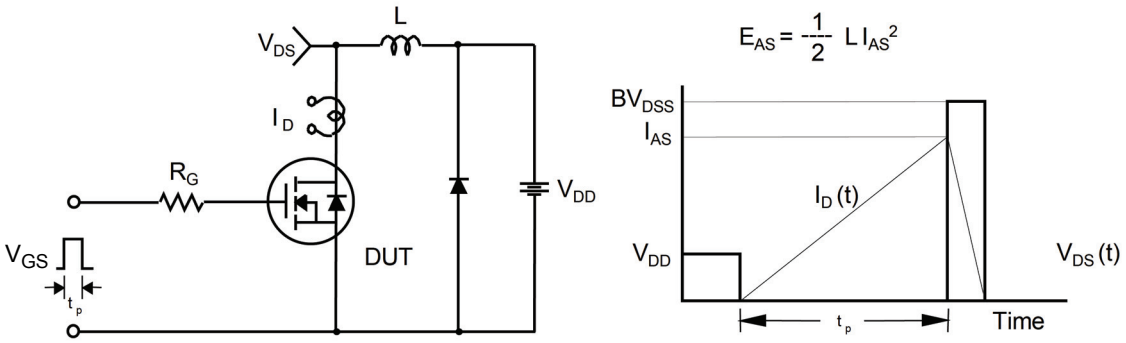


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

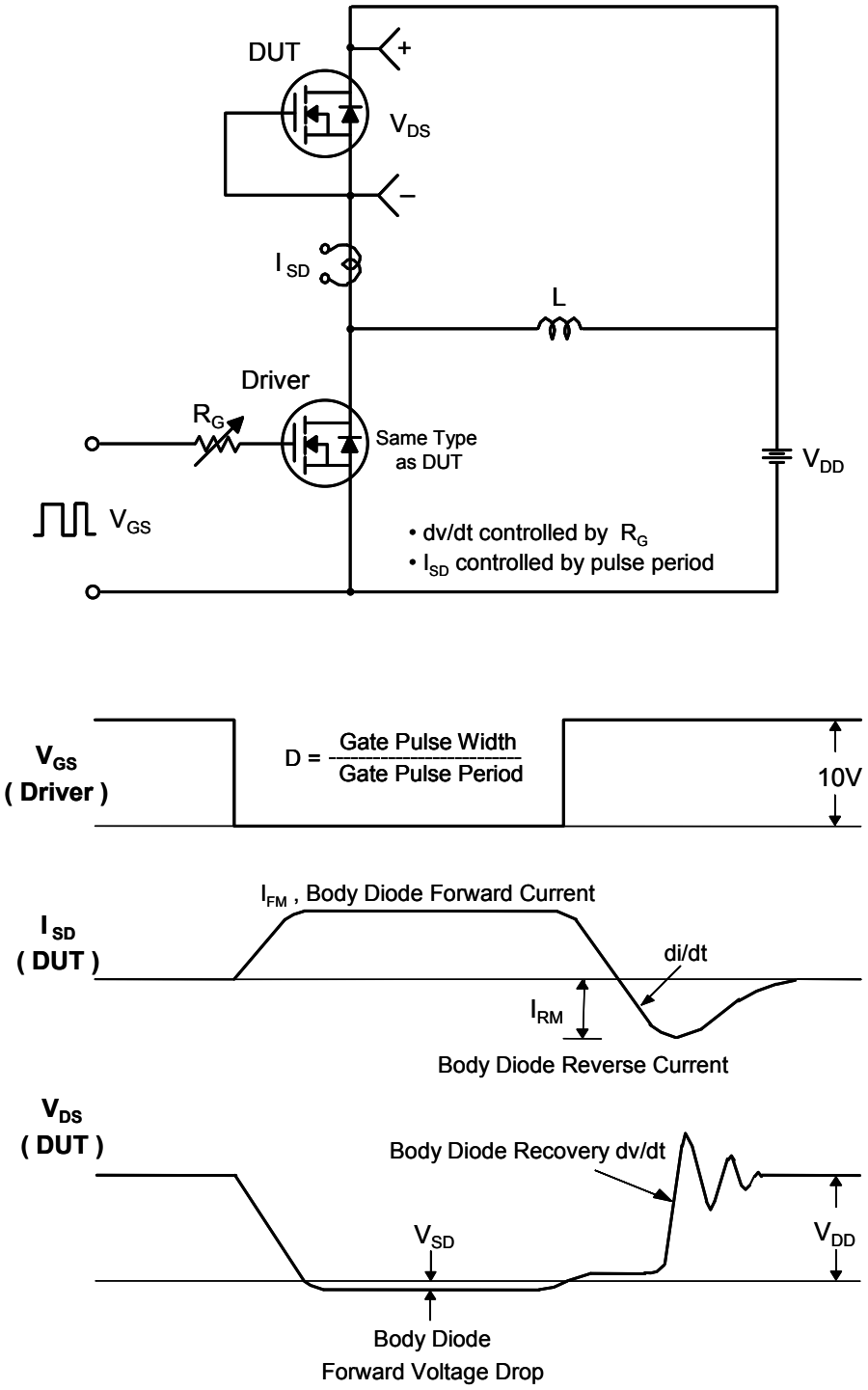
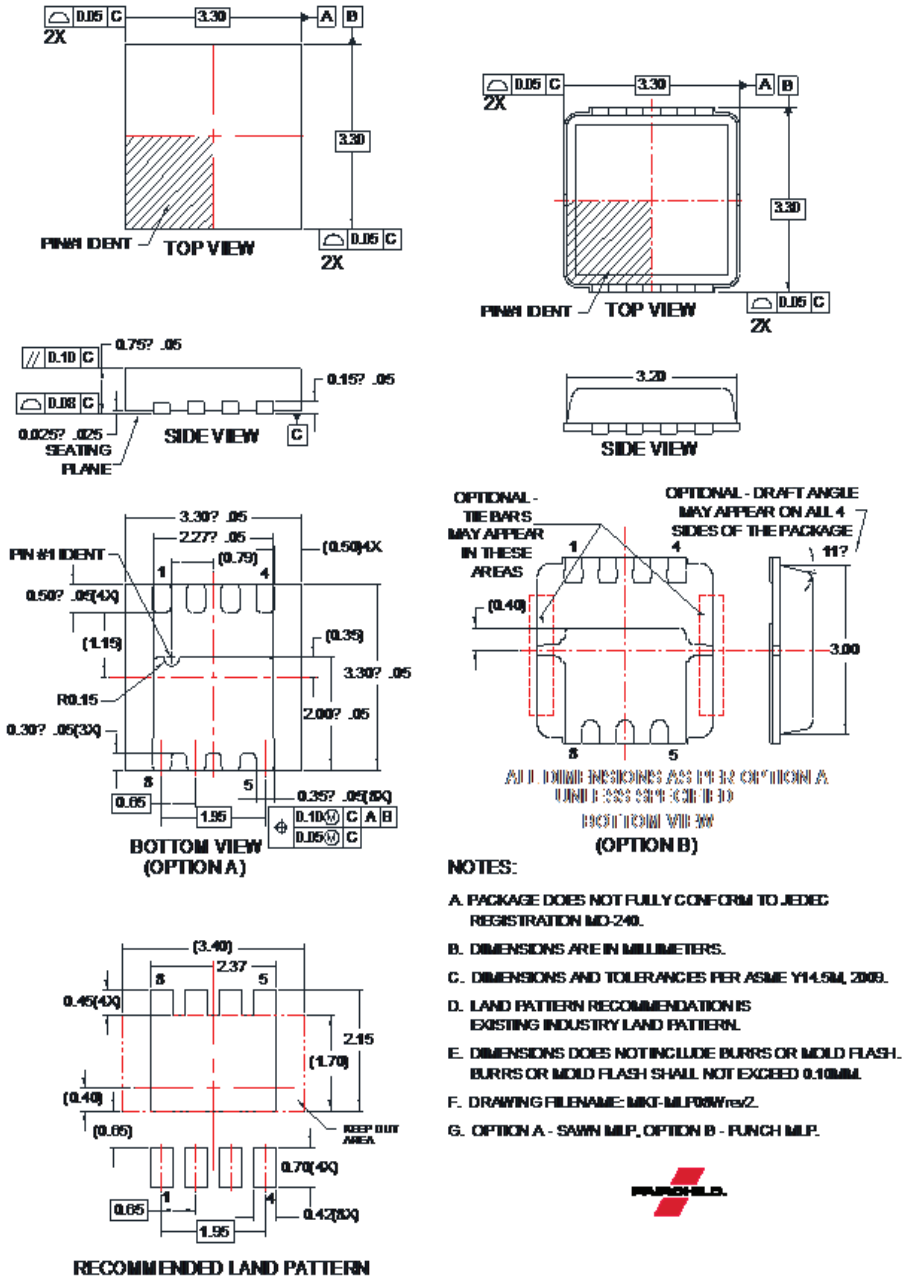


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



NOTES:

A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-240.

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.

D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

E. DIMENSIONS DOES NOT INCLUDE BURRS OR MOLD FLASH. BURRS OR MOLD FLASH SHALL NOT EXCEED 0.10MM.

F. DRAWING FILENAME: MKT-MLP08Wrev2.

G. OPTION A - SAWN MLP, OPTION B - PUNCH MLP.

Figure 16. MLP 3.3x3.3 8-Lead (Power 33)

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Datasheet Identification	Product Status	Definition
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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I68

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